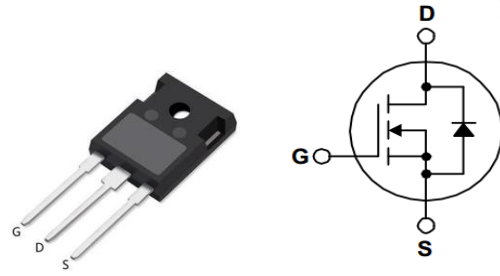


TH55N25PKH

250V 55A 55mΩ Silicon N-Channel Planar Power MOSFET

Features of this MOSFET are 150°C operating junction temperature and high repetitive peak current capability. These features combine to make this MOSFET a highly efficient, robust and reliable device for PDP driving applications.



Package view and circuit symbol

General Features

- $V_{DS}=250V, I_D=55A$
- Low ON Resistance, $R_{DS(on), typ.}=55m\Omega @ V_{GS}=10V, I_D=27.5A$
- Low reverse transfer capacitance
- Low Qg for fast response
- Short fall & rise times for fast switching
- 100% single pulse avalanche energy Test

Applications

- Power switching application
- Digital amplifier
- Adapter and charger

Key Performance Parameters

Parameter	Value	Unit
$V_{DSS}, \min @ T_J = 25^\circ C$	250	V
$T_J, \text{maximum junction temperature}$	150	°C
$I_D @ T_C = 25^\circ C (\text{Silicon Limit})$	55	A
$I_{D,pulse} @ T_C = 25^\circ C, t_p \text{ limited by } T_{Jmax.}$	220	A
$R_{DS(on), typ.} @ T_J = 25^\circ C, V_{GS} = 10V$	55	mΩ
$E_{AS}, \text{typ.} @ T_J = 25^\circ C$	1125	mJ



Marking Information

Product Name	Package	Marking
TH55N25PKH	TO-247H	TH55N25PKH

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Maximum Ratings (T_J = 25°C unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain to Source Voltage		V _{DSS}	250	V
Gate to Source Voltage		V _{GSS}	±30	V
Drain Current _(Silicon limit)	T _C =25°C	I _D	55	A
Pulsed Drain Current	T _C =25°C tp limited by T _{vjmax}	I _{DM}	220	A
Avalanche energy, single pulse	L=10mH, R _g =25Ω	E _{AS}	1125	mJ
Power Dissipation	T _C =25°C	P _D	347	W
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 To +150	°C
Lead Temperature for Soldering Purposes		T _L	270	

Thermal Characteristics

Parameter	Symbol	Max Value	Unit
Thermal Resistance, Junction-to-Case	R _{thJC}	0.36	°C/W
Thermal Resistance, Junction-to-Ambient	R _{thJA}	40	

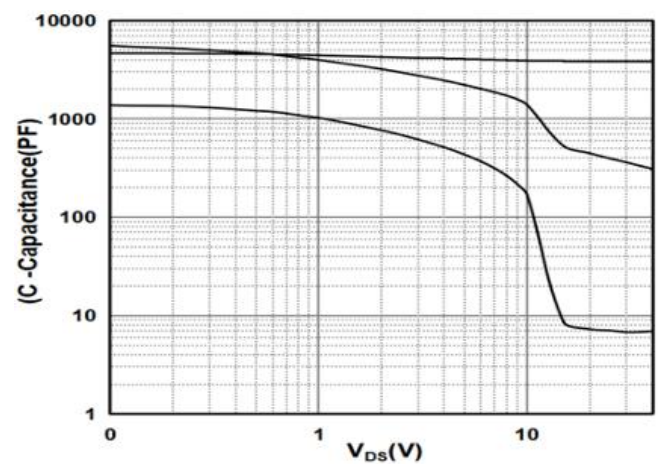
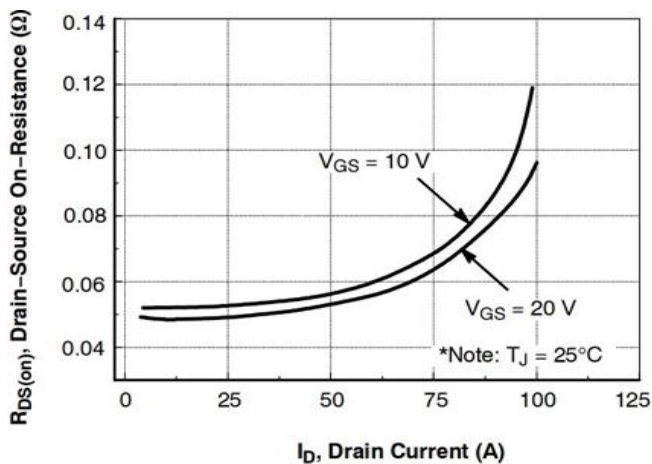
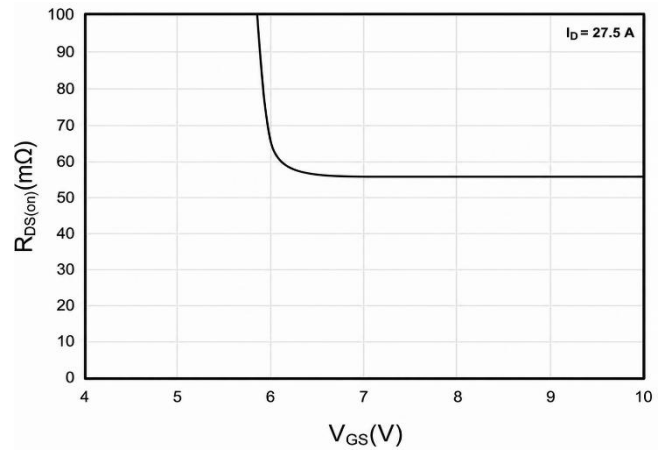
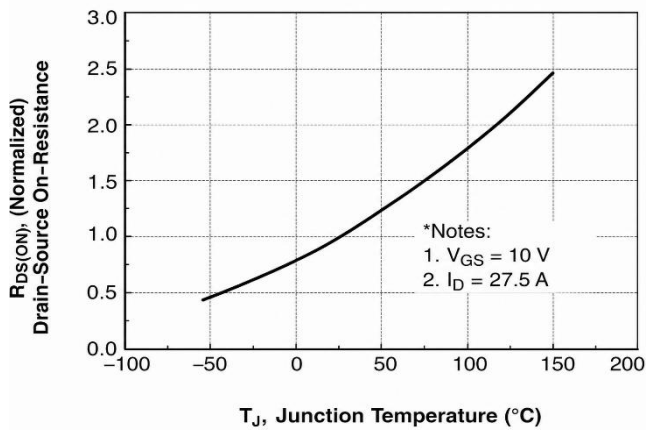
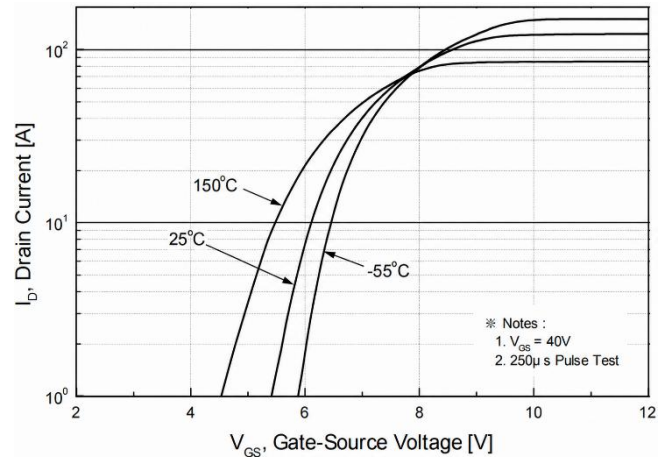
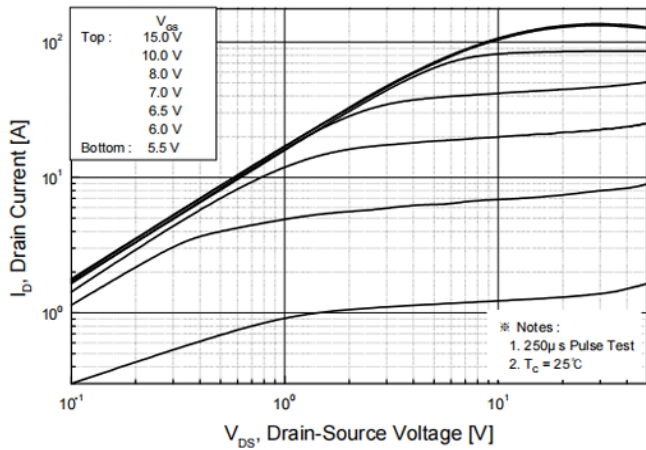
Electrical Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise specified)

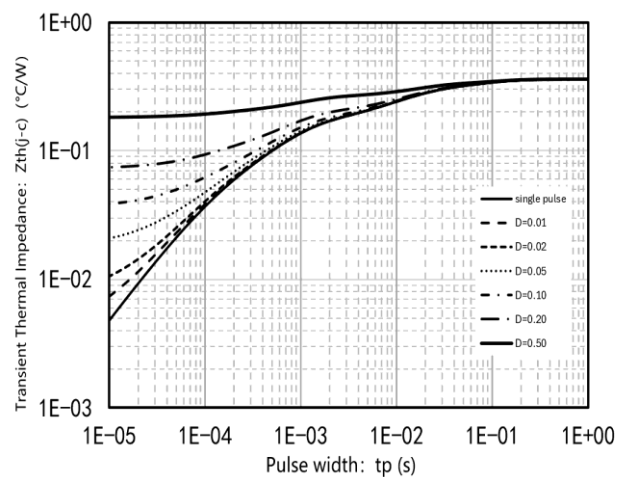
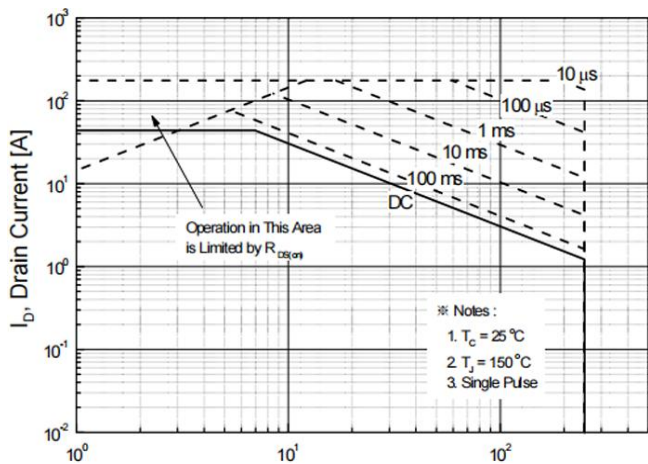
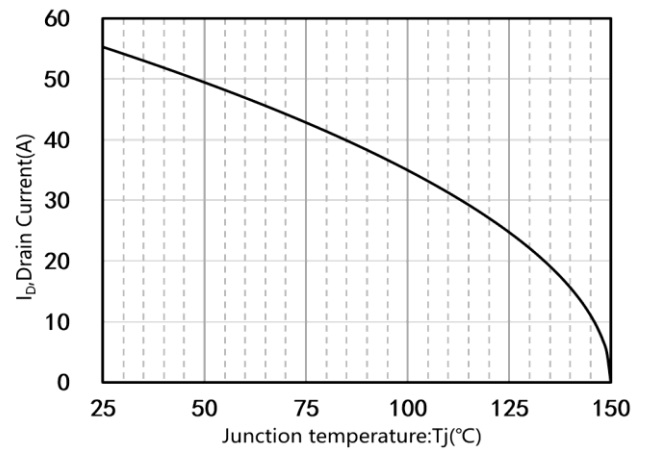
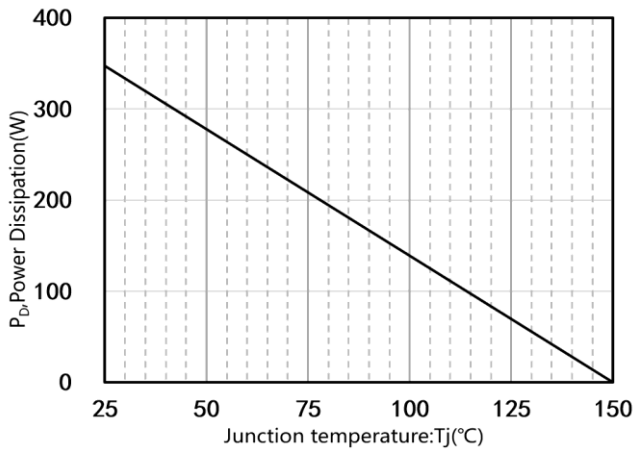
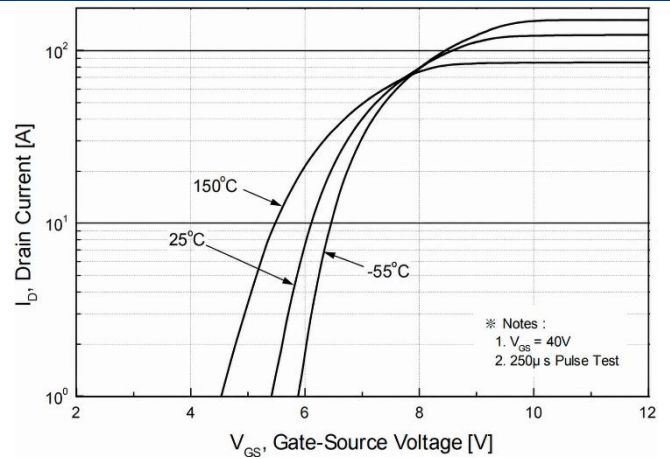
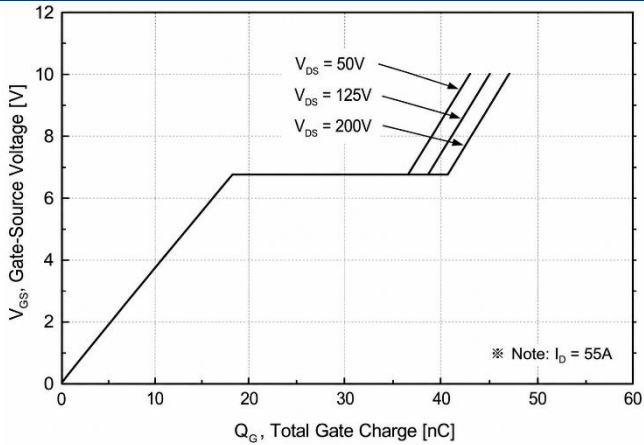
Parameter	Symbol	Test Condition	Value			Unit
			min.	typ.	max.	
Drain-to-Source Breakdown Voltage	$B_{V_{DS}}$	$V_{GS}=0V, I_D=250\mu A$	250	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS}=0V$ $V_{DS}=V_{DSS}$ $T_J=25^\circ\text{C}$	-	-	1	μA
		$V_{GS}=0V$ $V_{DS}=80\%V_{DSS}$ $T_J=125^\circ\text{C}$	-	-	10	
Gate-to-Source leakage Current	I_{GSS}	$V_{GS}=\pm 30V, V_{DS}=0V$	-	-	± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS}=V_{DS}$, $I_D=250\mu A$ $T_J=25^\circ\text{C}$	2.0	-	4.0	V
Drain-Source on-state resistance	$R_{DS(on)}$	$V_{GS}=10V$, $I_D=27.5A$ $T_J=25^\circ\text{C}$	-	55	66	$m\Omega$
Gate resistance	R_g	$V_{GS}=0V, V_{DS}=0V, f=1\text{MHz}$	-	1	-	Ω
Transconductance	g_{fs}	$V_{DS}=40V, I_D=27.5A$	-	28	-	S
Input Capacitance	C_{iss}	$V_{DS} = 25V, V_{GS} = 0V$, $f = 1\text{MHz}$	-	3875	-	pF
Output Capacitance	C_{oss}		-	395	-	
Reverse Transfer Capacitance	C_{rss}		-	6.8	-	
Total Gate Charge	Q_g	$V_{DS} = 200V, V_{GS} = 0/10V$, $I_D = 55A$	-	45	-	nC
Gate- Source charge	Q_{gs}			17		
Gate-Drain charge	Q_{gd}			25		
Turn-On Delay Time	$t_{d(on)}$	$V_{DS} = 125V$	-	53	-	ns
Turn-Off Delay Time	$t_{d(off)}$	$V_{GS} = 10V$	-	86	-	
Rise time	t_r	$I_D = 55A$ $R_G = 25\Omega$	-	398	-	
Fall time	t_f	$T_J = 25^\circ\text{C}$	-	116	-	

Diode Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise specified)

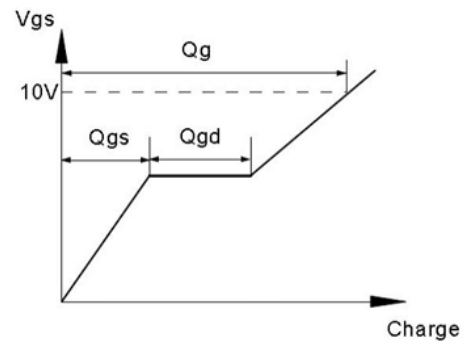
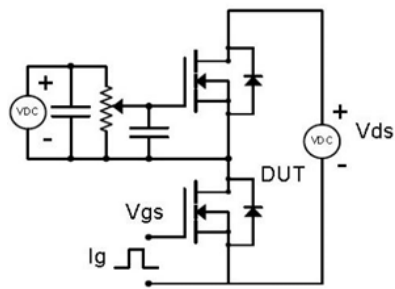
Parameter	Symbol	Test Condition	Value			Unit
			min.	typ.	max.	
Diode Continuous Forward Current	I_S	$T_C=25^\circ\text{C}$	-	-	55	A
Pulsed Diode Forward Current	I_{SM}		-	-	220	
Diode Forward Voltage	V_{SD}	$I_S = 55A$ $T_J = 25^\circ\text{C}$	-	-	1.5	V
Reverse Recovery Time	t_{rr}	$V_R = 100V, I_S = 55A$,	-	196	-	ns
Reverse Recovery Charge	Q_{rr}	$di_S/dt = 100A/\mu s, T_J = 25^\circ\text{C}$	-	1.5	-	μC

Typical Performance Characteristics

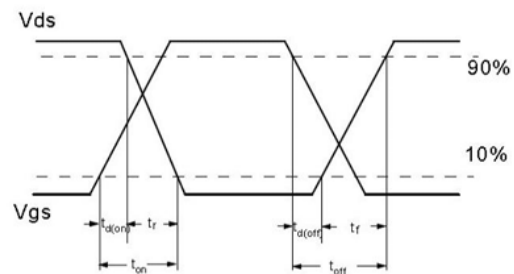
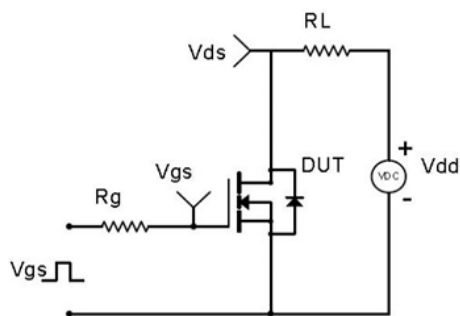




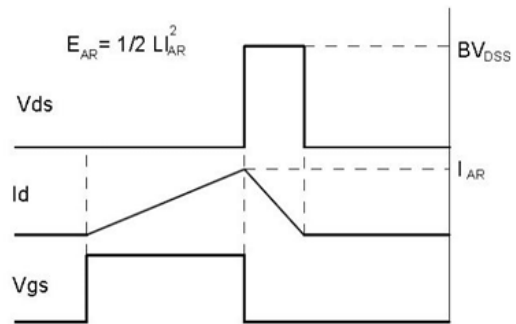
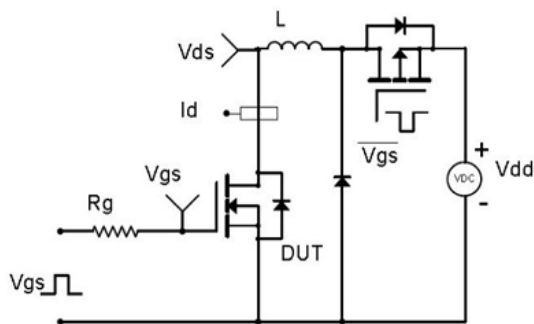
Test Circuit & Waveform



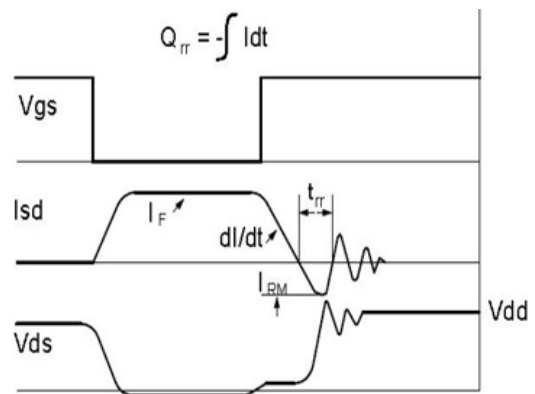
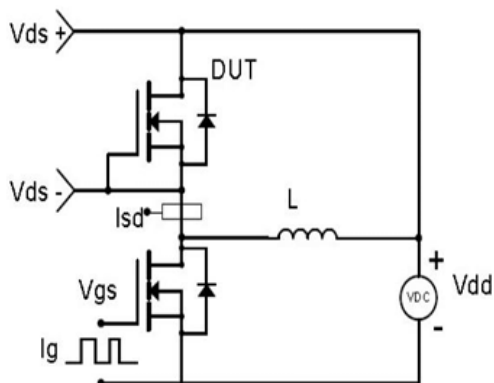
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



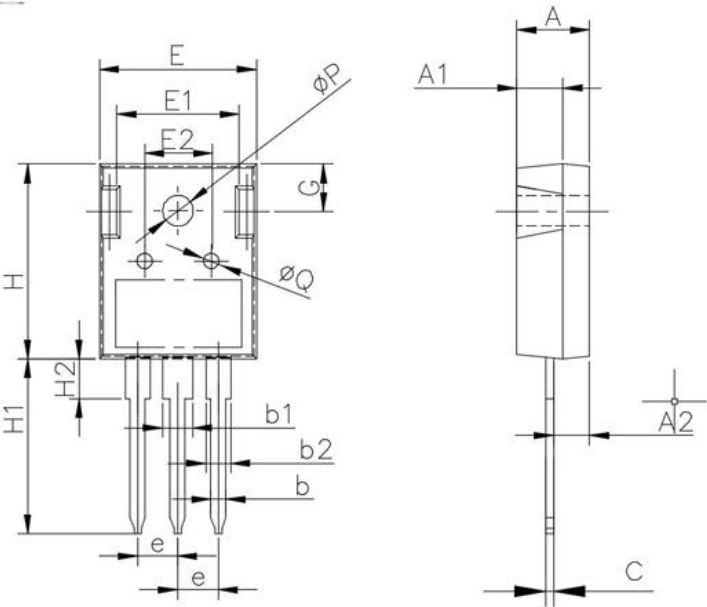
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

Package Information

基本尺寸



Symbol	单位 mm		
	Min	Nom	Max
A	4.80	5.00	5.20
A1	2.80	3.00	3.20
A2	2.20	2.40	2.60
b	1.05	1.20	1.35
b1	2.80	3.00	3.20
b2	1.80	2.00	2.20
c	0.50	0.60	0.70
e	5.35	5.45	5.75
E	15.6	15.80	16.0
E1	12.3	12.50	12.7
E2	6.00	6.20	6.40
H	20.8	21.0	21.2
H1	19.5	20.0	20.5
H2	3.70	4.00	4.30
G	5.70	5.90	6.10
ΦP	3.30	3.50	3.70
ΦQ	2.30	2.50	2.70

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